



100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	Package	I _D T _C = +25°C	
100V	$9.5 \text{m}\Omega @V_{GS} = 10V$	TO220AB	108A	

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

Applications

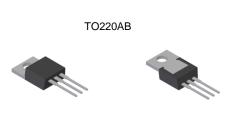
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

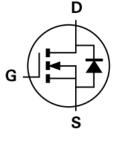
Features

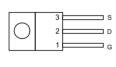
- Rated to +175°C Ideal for High Ambient Temperature Environments
- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO220AB
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram Below
- Weight: TO220AB 1.85 grams (Approximate)







Top View Bottom View

Equivalent Circuit

Top View Pin Out Configuration

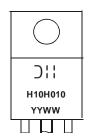
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH10H010LCT	TO220AB	50 pieces/tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



☐ H= Manufacturer's Marking
H10H010 = Product Type Marking Code
YYWW = Date Code Marking
YY or <u>YY</u> = Last Two Digits of Year (ex: 18 = 2018)
WW or <u>WW</u> = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	100	V	
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	108 76	А
Maximum Continuous Body Diode Forward Current	T _C = +25°C	I _S	90	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	92	Α
Avalanche Current, L = 0.3mH (Note 7)	I _{AS}	10	Α	
Avalanche Energy, L = 0.3mH (Note 7)		E _{AS}	15	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	P _D	2.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	61	°C/W
Total Power Dissipation	T _C = +25°C	P _D	166	W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	0.9	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +175	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

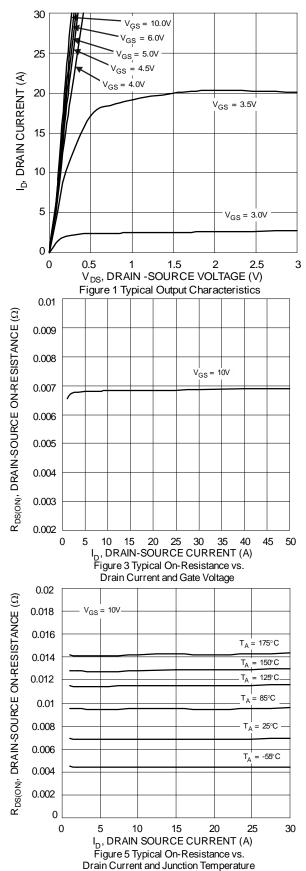
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	_	1	μA	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(TH)}	1.4	1.9	3.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	1	6.9	9.5	mΩ	$V_{GS} = 10V, I_D = 13A$	
Diode Forward Voltage	V_{SD}	-	0.8	1.3	V	$V_{GS} = 0V, I_{S} = 13A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}		4166	_		$V_{DS} = 50V$, $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss		764	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	44	_			
Gate Resistance	R_{G}	_	2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	58.4	_		V _{DD} = 50V, I _D = 13A, V _{GS} = 10V	
Gate-Source Charge	Q _{gs}		11.4	_	nC		
Gate-Drain Charge	Q _{gd}		14.2	_			
Turn-On Delay Time	t _{D(ON)}		11.6	_		$V_{DD} = 50V, V_{GS} = 10V,$ $I_{D} = 13A, R_{G} = 6\Omega$	
Turn-On Rise Time	t _R		14.1	_			
Turn-Off Delay Time	t _{D(OFF)}	_	42.9	_	ns		
Turn-Off Fall Time	t _F	_	22	_			
Reverse Recovery Time	t _{RR}	_	49.8	_	ns	-I _F = 13A, di/dt = 100A/μs	
Reverse Recovery Charge	Q_{RR}	_	85.1		nC		

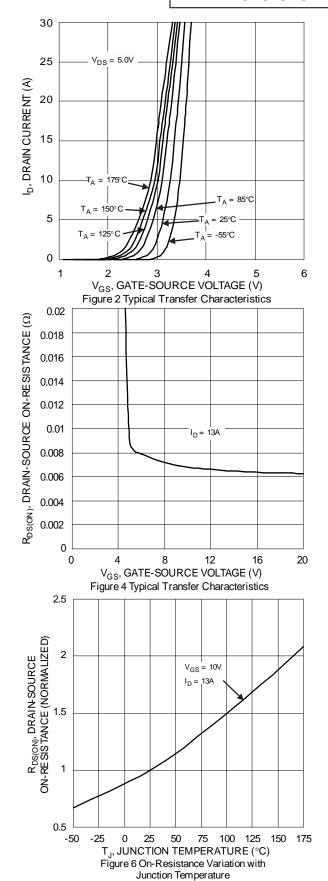
Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

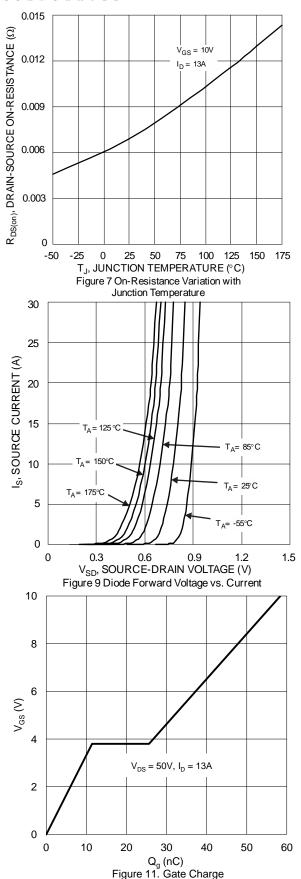


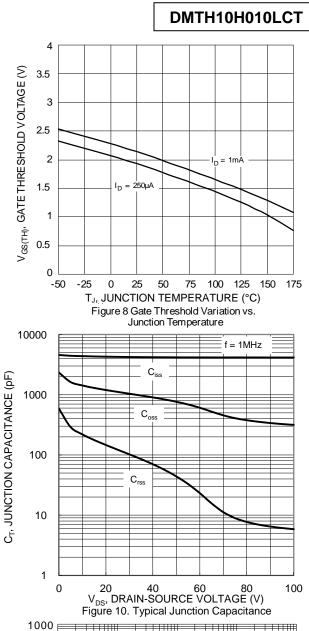


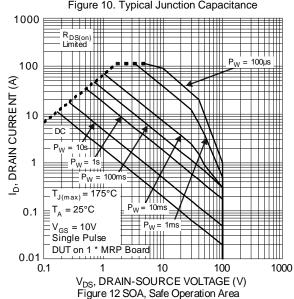




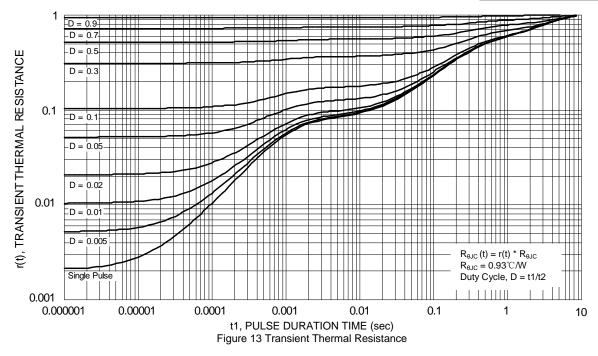








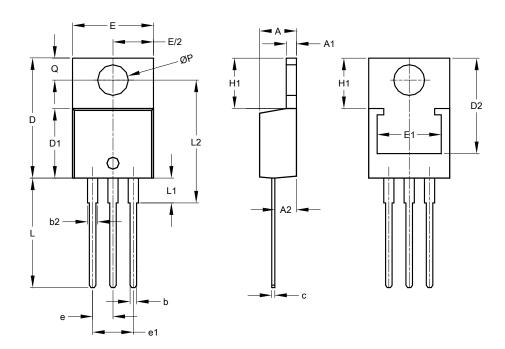




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220AB



10220AB						
Dim	Min	Max	Тур			
Α	3.56	4.82	-			
A 1	0.51	1.39	-			
A2	2.04	2.92	-			
b	0.39	1.01	0.81			
b2	1.15	1.77	1.24			
С	0.356	0.61	-			
D	14.22	16.51	-			
D1	8.39	9.01	-			
D2	11.45	12.87	-			
е	-	-	2.54			
e1	-	-	5.08			
Е	9.66	10.66	-			
E1	6.86	8.89	-			
H1	5.85	6.85	-			
L	12.70	14.73	-			
L1	-	4.42	-			
L2	15.80	17.51	16.00			
Р	3.54	4.08	-			
Q	2.54	3.42	-			
All Dimensions in mm						

TO220AB



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